Im purity-induced stabilization of Luttinger liquid in quasi-one-dim ensional conductors

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Abstract

It is shown theoretically that the Luttinger liquid phase in quasi-one-dimensional conductors can exist in the presence of impurities in a form of a collection of bounded Luttinger liquids. The conclusion is based upon the observation by K ane and F isher that a local impurity potential in Luttinger liquid acts, at low energies, as an in nite barrier. This leads to a discrete spectrum of collective charge and spin density uctuations, so that interchain hopping can be considered as a small parameter at temperatures below the minimum excitation energy of the collective modes. The results are compared with recent experimental observation of a Luttinger-liquid-like behavior

in thin NbSe3 and TaS3 wires.

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Electronic properties of one-dimensional (1D) metals are known to be very dierent from those of ordinary three-dimensional (3D) metals (for a review see Ref.[1, 2, 3]). 3D electron gas is well described by Landau's Ferm i-liquid picture in which interaction modi es free electrons making them quasiparticles that behave in many respects like non-interacting electrons. In contrast to the 3D case, in 1D electronic system sthe Ferm i-liquid picture breaks down even in the case of the arbitrarily weak interaction. In 1D metals, the single-electron quasiparticles do not exist, and the only low energy excitations turn out to be charge and spin collective modes with the sound-like spectrum. These modes are dynamically independent giving rise to a spin-charge separation in 1D systems. Furthermore, correlation functions at large distances and times decay as a power law with interaction dependent exponents. Such a behavior has been given a generic name Luttinger liquid [4].

The concept of Luttinger liquid is of great interest in view of its application to real physical systems, such as carbon nanotubes and semiconductor heterostructures with a con ning potential (quantum wires and quantum Halle ect edge states). The case of a special interest are quasi-1D conductors, i. e., highly anisotropic 3D conductors with chainlike structure. Num erous experim ental studies of both organic and inorganic q1D conductors at low tem peratures typically dem on strate broken-sym m etry states, like superconductivity, spin-or charge-density wave (CDW) states, and a metallic behavior above the transition tem perature with non-zero single-particle density of states at Ferm i energy. For instance, the most studied inorganic quasi-1D metals undergo the Peierls transition from metallic state either to a sem iconducting CDW state (e.g., blue bronze K<sub>0.3</sub>M oO<sub>3</sub>, TaS<sub>3</sub>, (TaSe<sub>4</sub>)<sub>2</sub>I etc.) or to sem in etallic CDW state (NbSe3) [5]. Typically, this transitions occur in the tem perature range 50 - 250 K. From the theoretical point of view, the form ation of Luttinger liquid in quasi-ID conductors at low enough temperatures is also problematic because of the instability towards 3D coupling in the presence of arbitrarily small interchain hopping [6, 7, 8, 9, 10]. So the interchain hopping induces a crossover to 3D behavior at low energies, while Luttinger liquid behavior can survive only at high enough energy scale where it is not a ected by 3D coupling.

In contrast to the interchain hopping, the Coulomb interaction between the electrons at dierent chains does not destroy the Luttinger liquid state, the main dierence from the 1D case being the absence of simple scaling relations between the exponents of the various correlation functions [11, 12, 13, 14].

However, in recent experimental studies of temperature and eld dependence of conductivity of TaS<sub>3</sub> and NbSe<sub>3</sub> in nanoscale-sized crystals a transition from room-temperature metallic behavior to nonmetallic one accompanied by disappearance of the CDW state at temperatures below 50 - 100 K was observed [15, 16, 17]. The low temperature non-metallic state was characterized by power law dependencies of the conductivity on voltage and temperature like that expected in Luttinger liquid, or by more strong temperature dependence corresponding to the variable-range hopping. Resembling dependencies of conductivity were reported although in focused-ion beam processed or doped relatively thick NbSe<sub>3</sub> crystals [17]. Hopping conductivity was also detected in dirty quasi-1D conductors KCP and organic TCNQ-based metals [18], while pure materials are known to undergo the Peierls transition to the CDW state.

First of all we start with the TL model ignoring interchain hopping integral  $t_{?}$  in order to formulate the problem in the zeroth approximation in  $t_{?}$ . Electronic operators for right (r = +1) and left (r = -1) moving electrons with spin s are given in terms of phase elds as (see Ref.[1, 3])

$$_{r;s}(x) = \lim_{t \to 0} \frac{e^{irk_F x}}{2} _{r;s}e^{iA_r}; \quad A_r = \frac{1}{2}[ r + s(r)]$$
 (1)

here phase elds (x) are related to charge ( = ) and spin ( = ) densities, while elds

(x) are related to the momentum operators  $= (1=) e_x$  canonically conjugate to . Further,  $_{r;s}$  are M a jorana ("real") Ferm ionic operators that assure proper anticom mutation relations between electronic operators with dierent spin s and chirality r, and the cut o length is assumed to be of the order of interatom ic distance.

We describe the intrachain properties of the system by the standard TL Ham iltonian [1,3] with added  $2k_F$  in purity backscattering term [2]. In the bozonized form it reads

where v are velocities of the charge ( = ) and spin ( = ) modes,  $K = v_F = v$  is the standard Luttinger liquid parameter describing the strength of the interaction,  $V_0$  and d are amplitude and radius of the scattering potential, respectively.

K ane and F ischer [19] found that the backscattering impurity potential for repulsive potential (K < 1) ows to in nity under scaling. Their arguments were generalized by Fabrizio and G ogolin [22] to the case of many impurities. It was shown that the impurity potential can be considered as electively in nite provided that the mean distance, I, between impurities satis es the condition

$$1 \quad \frac{1}{k_{F}} \quad \frac{D}{V_{0}} \quad \stackrel{2=(1 \quad K \quad )}{;} \tag{3}$$

where D is the bandwidth. We assume that the impurity potential is of atom ic scale,  $V_0 \le D$ , and the interaction between electrons is not too weak, (i. e., K is not too close to 1). Then condition (3) is satisfied for l  $1=k_F$  which is of the order of interatom ic distance. So the limit of strong impurity potential should be a good approximation in a wide range of impurity concentrations.

Further, , and must obey the commutation relations (see Ref.[1, 2, 3]) ensuring anticommutation of electronic operators (1). Using then the analogy of Eq.(2) with the Ham iltonian of an elastic string strongly pinned at impurity sites, we can write down solutions for the phase operators and in the region between impurity positions at  $x = x_i$  and  $x_{i+1}$  as

where  $\mathbf{x} = \mathbf{x}$   $\mathbf{x}_i$ ,  $\mathbf{l}_i = \mathbf{x}_{i+1}$   $\mathbf{x}_i$ ,  $\mathbf{q}_n = \mathbf{n} = \mathbf{l}_i$ ,  $\mathbf{l}_i$  is the modulo 2 residue of  $2\mathbf{k}_F \mathbf{x}_i$ . Further,  $\mathbf{N}_i = (\mathbf{N}_{i+1} + \mathbf{N}_{i+1}) = \overline{2}$ ,  $\mathbf{N}_i = (\mathbf{N}_{i+1} + \mathbf{N}_{i+1}) = \overline{2}$ , and  $\mathbf{N}_{i+1} = (\mathbf{N}_{i+1} + \mathbf{N}_{i+1}) = \overline{2}$ , and  $\mathbf{N}_{i+1} = (\mathbf{N}_{i+1} + \mathbf{N}_{i+1}) = \overline{2}$ , and  $\mathbf{N}_{i+1} = \mathbf{N}_i = \mathbf{N}_i$  is the number of extra electrons with spin up (down) in the region between i-th and (i+1)-th impurities, and, nally,  $\mathbf{l}_i$  is the phase canonically conjugate to  $\mathbf{N}_i = \mathbf{l}_i$ .

Excitation spectra of the eigenm odes are  $!=n!_1;$   $vq_n$  where  $!_1;=v=l_i$  is the minimum excitation frequency for mode .

Note that if we consider the open boundary conditions at the sample ends, x=0, and, x=L, (instead of periodic boundary conditions that are commonly used) then operators s in Eq.(1) are the same for electrons going right and left. In this case, the electron eld operator, s(x)=s+(x)+s=(x), vanishes at impurity positions, s=s+(x)+s=(x)+s=(x), and expressions for the phase elds between the impurity sites turn out to be similar to those found for bounded 1D Luttinger liquid in Refs.[22, 23, 24], the main dierence being the summation over s=s+(x)+s=(x)

Now we consider the role of interchain hopping adding to (2) the hopping Ham iltonian

$$H_{?} = t_{?} \qquad dx_{r;s,m}^{+}(x)_{r;s,m}(x) + HC$$

$$= X \qquad \frac{X}{Z} \qquad \frac{it_{?} r_{;s,m} r_{;s,m}}{it_{?} r_{;s,m} r_{;s,m}} \left[ sin(A_{r,m} A_{r,m}) + sin(A_{r,m} A_{r,m} + 2irk_{F}x) \right]; \qquad (5)$$

where indices n and m denoting the chain numbers related to the nearest neighbors are added.

A rgum ents by Schulz [8] on instability of the Luttinger liquid in the presence of the interdhain hopping were based on calculations of tem perature dependence of the therm odynam ic potential at low tem peratures. So we calculate contribution of the interchain hopping to the therm odynam ic potential per unit volum e given by the standard expression [25]

= 
$$T \ln hS i=V$$
;  $S = T \exp \begin{pmatrix} Z_{1=T} & ! \\ & H_{?} ()d ; \end{pmatrix}$  (6)

where V is the volume, T stands for imaginary time ordering, and h imeans thermodynamic averaging over the unperturbed state.

At tem peratures T  $!_1$ , the discreteness of the excitation spectrum can be neglected, hence, according to Refs. [6, 7, 8, 9, 10], interchain hopping is expected to give signicant

contributions destroying the Luttinger liquid. We exam in the opposite  $\lim$  it, T ! 1; , which does not exist in pure in nite Luttinger liquid.

Consider rst the second order correction in  $t_2$ . The leading contribution to hSi in Eq.(6) is given by items in which the term related to a given chain contains contributions from the electrons with the same chirality,  $r_1$ , only,

$$\frac{X}{x} = \frac{t_{?}^{2}}{8^{2}} = \frac{Z}{2} = \frac$$

where  $1 = fx_1$ ; 1g and  $2 = fx_2$ ; 2g. O ther items in which the terms related to the same chain contain contributions from electrons moving both left and right gives mall contribution, and we do not discuss them in details.

Then we use Eq.(4) in (1) and calculate average in (7) using the relation

$$hT e^{iA_{r,m} (1)} e^{iA_{r,m} (2)} i = e^{\frac{1}{2}hA_{r,m}^2 (1) + A_{r,m}^2 (2)} 2T [A_{r,m} (1)A_{r,m} (2)]i};$$
(8)

N eglecting sm all corrections / exp  $\left[\begin{array}{c} \frac{!}{T} \end{array}\right]$  due to P lanck's distribution functions, we nd for the average in the exponent

$$hT A_r(1)A_r(2)i = \frac{1}{8} \ln^4 \frac{(\cosh z + \cos y)^{(K - K^{-1})}}{(\cosh z + \cos y)^{(K + K^{-1})}} + itan^{-1} \frac{\sin y}{e^z + \cos y};$$
 (9)

where  $y=\frac{(x_1-x_2)}{l_i}$ ,  $z=\frac{(+v-j_1-2)!}{l_i}$  (chain indices are dropped for brevity here).

In the integrations over 1 and 2, the leading contributions comes from region 1 2, i. e., jy j 1, z 1 where expression (7) reduces to

$$\frac{t_{?}^{2} m L}{2^{2} T} = \frac{\cos[(r + r^{0})k_{F} (x + r^{0})] dx d}{2}$$

$$= : [(1 + r^{0})^{2} + (x + r^{0})^{2}]^{1+2}$$
(10)

where  $=\frac{v}{4}$ ,  $=\frac{1}{4}$  (K + 1=K 2),  $=j_1$   $_2j$  x  $=x_1$   $x_2$ , and m is the number of the nearest-neighbor chains. Contribution to expression (7) from integration over region y y y 1, z 1, is small,  $(=l_i)^2$ , = + , because is not too small in the assumed case of the not too small interaction (cf. Eq. (3)).

Additional items in hSi in Eq.(6) in which the terms related to the same chain contain contributions from electrons moving both left and right is smaller than that given by Eq. (10) by factor  $(=l_i)^{K-K}$ . For reasonable values of K, this contribution is small and can be neglected.

Sim ilarly, the leading contribution to from higher-order terms in series expansion of the exponential in Eq.(6) was found to come from even powers 2n in  $t_2$  that can be

represented as a sum of (2n 1)!! item s like (7) with almost coinciding times and coordinates. Therefore, summing up the leading contributions and inserting them into Eq.(6) we can calculate the variation of the thermodynamic potential per single chain and per unit length

$$= a \frac{t_2^2 m}{{}^2V_F}; a = \frac{Z}{2} \frac{(1 + \cos 2k_F x) dxd}{(1 + \cos 2k_F x)^2 + x^2]^{1+2}};$$
 (11)

For moderate repulsion, 1, a 1. In the lim it of strong repulsion, K K 1, a is small, a  $K^2$ .

Thus is much smaller than the thermodynamic potential of purely 1D Luttinger liquid,  $_0$   $_{K}^{\frac{1}{K}}+\frac{1}{K}$  "  $_{F}^{r}k_{F}$  ,

$$= 0 \frac{t_?}{T_F}^2;$$

and tem perature-dependent corrections to Eq.(11) are determ ined by small thermally activated contributions / exp [  $\frac{!}{T}$ ].

Now we calculate modi cation of the one-particle Green's function due to the interchain hopping.

$$G(1;1^0) = hT(1)(1^0)Si=hSi:$$
 (12)

Again, we consider the low-tem perature lim it, T  $!_1$ ; , non-existing in pure in nite system. Consider rst the second order correction in  $t_2$  to the Green's function of pure 1D system,  $G_0(1;1^0)$ .

$$G_2(1;1^0) = hT (1) (1^0)S_2i + hT (1) (1^0)ihS_2i;$$
 (13)

Calculation is similar to that considered above, (cf. (7-9)). However, in contrast to the case of the therm odynam ic potential where the leading contribution was given by regions of almost coinciding values of times and coordinates, such contributions from two terms in (9) cancel each other. So the second-order correction is estimated as

$$G_2(1;1^0) < \frac{t_2 1^{\frac{1}{2}}}{v_F} - \frac{1}{1} G_0(1;1^0)$$
:

Estimation of the fourth order correction in  $t_2$  gives  $G_4$  ( $t_2 = v_F$ )<sup>2</sup> (=1) <sup>2</sup>  $G_2$ . Therefore, we conclude that at T ! 1; the interchain hopping gives small corrections to the one-particle G reen's function, provided

$$\frac{t_{?} 1}{v_{F}} \frac{1}{1} = \frac{t_{?}}{1} = \frac{t_{?}}{1} = \frac{2}{1} = 1;$$
 (14)

where we estimated the cut-o parameter as  $1=k_F$ .

So far we considered the TL model in which interaction is described by coupling constants related to forward—and backscattering. In order to make comparison with experimental data we must consider a more realistic Coulomb potential. It is reasonable to assume that the long-range part of the interaction is dominated by the Coulomb potential, while the backscattering is described by relatively small coupling constant  $g_1$ . This enables us to concentrate on the spin isotropic case and to ignore the possibility of the spin gap. The problem of the long-range Coulomb potential on an array of chains was solved in Refs. [11, 12, 13]. It was found that interaction of electrons on a given chain is screened by the electrons on other chains, and the Coulomb interaction can be described by the TL Ham iltonian with coupling constants dependent on wave vector,

$$g_2 = g_4 = \frac{4 e^2}{s^2 (q_2^2 + q_2^2)};$$
 (15)

where s is the lattice period in the direction perpendicular to the chains, and ? is a background dielectric constant for the transverse direction. Coupling constants in spin channel remain una ected. In principle, the coupling constants must be determined by matrix elements of Coulomb potential that depend on details of wavefunctions and on chain arrangement, and must contain an in nite sum over transversal reciprocal lattice vectors. So expression (15) is not universal and depends on material.

Eq. (15) leads to q-dependent velocities

$$! = \frac{V_F}{K} q_k; \quad \frac{1}{K} = {\overset{v}{\overset{u}{U}}} \frac{1}{1 + \frac{\theta}{s^2 (q^2 + \frac{1}{2} q_0^2)}}; \quad \theta = {^2s^2} = \frac{8e^2}{hv_F}; \quad (16)$$

where is the inverse Thom as Ferm iscreening length.

We do not perform explicit calculations restricting ourselves to estimations. For the case of q-dependent coupling expressions for the therm odynamic potential and G reen's functions contain various integrals of correlation functions over  $q_2$ . One can show that the results obtained above can be generalized qualitatively to the case of long-range C oulomb interaction if we substitute  $q_2$  in Eq. (16) for its characteristic value,  $q_2$  =s. For example, integrals for corrections to the therm odynamic potential are dominated by close values of coordinates and times, similar to Eq. (10), and coupling parameters should be substituted by their averages over  $q_2$ ,

$$= \frac{1}{4} (\overline{K} + \overline{1 = K} + K + 1 = K$$
 4)  $\frac{1}{4} \frac{{"_Z}}{(2)^2} \frac{s^2 d^2 q_2}{(2)^2} K + \frac{1}{K} \frac{!}{K}$  2:

Note that  $\ell=8$  (c=v\_F), where is the ne structure constant. Since  $v_F$  is much smaller than the velocity of light, the factor  $\ell=1$  is large. For  $v_F=1$  is much smaller value for transition metal trihalcogenides,  $\ell=1$  is a specific parameters,  $v_F=1$  is much smaller than the velocity of light, the factor  $\ell=1$  is large. For  $v_F=1$  is much smaller than the velocity of light, the factor  $\ell=1$  is much smaller than the velocity of light, the factor  $\ell=1$  is much smaller than the velocity of light, the factor  $\ell=1$  is much smaller than the velocity of light, the factor  $\ell=1$  is much smaller than the velocity of light, the factor  $\ell=1$  is much smaller than the velocity of light, the factor  $\ell=1$  is much smaller than the velocity of light, the factor  $\ell=1$  is much smaller than the velocity of light, the factor  $\ell=1$  is large. For  $v_F=1$  is much smaller than the velocity of light, the factor  $\ell=1$  is large. For  $v_F=1$  is much smaller than the velocity of light, the factor  $\ell=1$  is large. For  $v_F=1$  is much smaller than the velocity of light, the factor  $\ell=1$  is large. For  $v_F=1$  is much smaller than the velocity of light, the factor  $\ell=1$  is much smaller than the velocity of light, the factor  $\ell=1$  is much smaller than the velocity of light. For  $\ell=1$  is much smaller than the velocity of light, the factor  $\ell=1$  is much smaller than the velocity of light. For  $\ell=1$  is much smaller than the velocity of light and  $\ell=1$  is much smaller than the velocity of light and  $\ell=1$  is much smaller than the velocity of light and  $\ell=1$  is much smaller than the velocity of light and  $\ell=1$  is much smaller than the velocity of light and  $\ell=1$  is much smaller than the velocity of light and  $\ell=1$  is much smaller than the velocity of light and  $\ell=1$  is much smaller than the velocity of light and  $\ell=1$  is much smaller than the velocity of light and  $\ell=1$  is much smaller than the velocity of light and  $\ell=1$  is much smaller than the velocity of light and  $\ell=1$  is much smaller than the velocity of light and  $\ell=1$  is much smaller than

Now we discuss conditions for observation of the Luttinger liquid in quasi-1D conductors stabilized by impurities. First we discuss the condition for the temperature  $\lim$  iting from above the region where the Luttinger liquid can exist. This condition reads, I: 1, . The minimal excitation energies, I: 1, can be estimated as

$$!_{1}$$
; =  $\frac{hv_F}{1} \overline{1=K}$   $"_F$   $\frac{1}{k_F} \overline{1}$   $\overline{1=K}$   $"_F$   $c_1 \overline{1=K}$ ;

where  $c_i$  stands for dim ensionless in purity concentration corresponding to number of im purities per one electron. As Ferm i energy in NbSe<sub>3</sub> and TaS<sub>3</sub> is about 1 eV, we obtain that  $l_1$ ; is about 100 K for impurity concentration  $c_i$  10  $^2$  10  $^3$ .

A nother condition to be full led is smallness of corrections to the Green's function due to interchain hopping. A coording to Eq.(14) the corrections are small provided

$$\frac{t_2}{u_E}$$
  $^2$   $c_i^2$   $^2$  1:

If the interaction is strong enough, > 1, this condition is not more strict than the condition for the limiting temperature discussed above. For lower strength of interaction, < 1, this condition reads

$$c_{i}$$
  $\frac{t_{?}}{m_{E}}$   $^{1=(2\ 2\ )}$ :

Estimating  $t_{?}$  as being of the order of the Peierls transition temperature,  $T_{P}$  100 200 K 0.01%, we not that this condition can be full led easily even at = 1=2 for relatively small in purity concentration,  $c_{i}$  10  $^{2}$ .

Thus we not that Luttinger liquid can be stabilized by impurities in relatively pure linear-dhain compounds at rather high temperatures corresponding to experimental observation Refs.[15, 16, 17] of the transition from metallic to non-metallic conduction characterized by power law dependencies of conductivity and by conductivity resembling the variable-range hopping. However, in order to make detailed comparison with the experimental data, calculation of the conductivity in a random network made of weakly coupled bounded Luttinger liquids is needed.

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